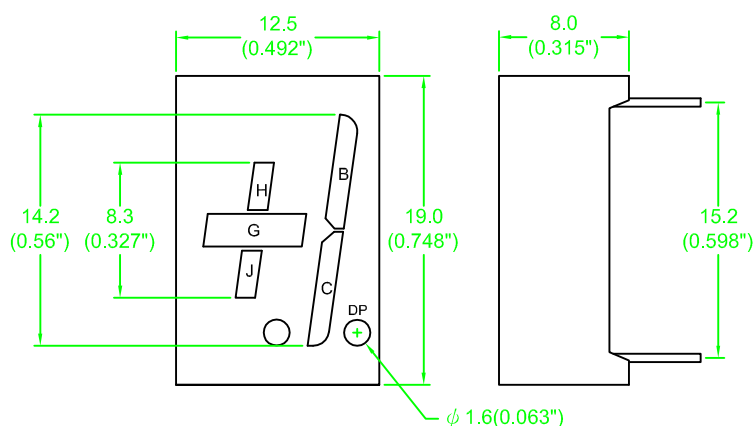
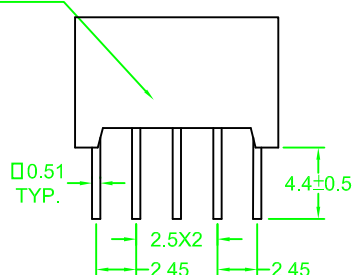


PACKAGE DIMENSION



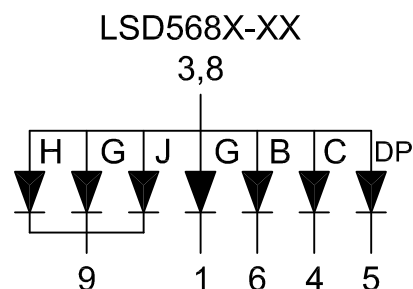
LSD568X-XX
LIGITEK



PIN NO.1 →

NOTE:1.All Dimension Are In Millimeters And (Inch)
Tolerance Is ± 0.25 (0.01") unless Otherwise Noted
2.Specifications are subject to change without notice.

INTERNAL CIRCUIT DIAGRAM



Connection To Electrical Schematic

Electrical connection

PIN NO.	LSD568X-XX		
1	Cathode G		
2	NC		
3	Common Anode		
4	Cathode C		
5	Cathode DP		
6	Cathode B		
7	NC		
8	Common Anode		
9	Cathode H,G,J		
10	NC		

• Part Selection And Application Information(Ratings At 25°C Ambient)

PART NO	CHIP		common cathode or anode	λ p (nm)	$\Delta \lambda$ (nm)	Electrial					IV-M
	material	emitted				Vf(v)			Iv(mcd)		
						Min	Typ	Max	Min	Typ	
LSD5682V-XX	GaP	Green	Common Anode	565	30	1.7	2.1	2.8	1.6	2.8	2:1
LSD5685-XX	GaAlAs	Red		660	20	1.5	1.7	2.4	2.0	3.5	2:1
LSD5684-XX	GaAsP/GaP	Orange		635	45	1.7	2.0	2.8	0.8	1.35	2:1
LSD5682-XX	GaP	Green		565	30	1.7	2.1	2.8	1.0	1.75	2:1

• Absoult Maximum Rating (Ta=25°C)

Parameter	Red			Green		Yellow			Orange		Unit	Remark
Forward Current Per Chip		SR		VG	G					E		
		40		30	30					30	mA	
Peak Current Per Chip (Duty 1/10,0.1mS Pulse Width)		200		120	120					120	mA	
Power Dissipation Per Chip	110			100					100		mW	
Derating Linear From 25℃ Per Chip	0.45			0.45					0.45		mA/℃	
Reverse Current Per Any Chip	10			10					10		μ A	
Operating Temperature	-25℃ TO +85℃											
Storage Temperature	-25℃ TO +85℃											

Solder Temperature 1-16 Inch Below Seating Plane For 3 Seconds At 260 °C

• Test Condition For Each Parameter

Parameter	Symbol	Unit	Test Condition
Forward Voltage Per Chip	Vf	volt	If=20mA
Luminous Intensity Per Chip	Iv	mcd	If=10mA
Peak Emission Wavelength	λ_p	nm	If=20mA
Spectral Line Half-Width	$\Delta \lambda$	nm	If=20mA
Reverse Current Any Chip	Ir	μ A	Vr=5V
Luminous Intensity Matching Ratio	IV-M		